

# PMZ1000UN N-channel TrenchMOS standard level FET

Rev. 2 — 17 September 2010

**Product data sheet** 

## 1. Product profile

### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

### **1.2 Features and benefits**

- Fast switching
- Low conduction losses due to low on-state resistance
- Saves PCB space due to small footprint (90 % smaller than SOT23)
- Suitable for use in compact designs due to low profile (55 % lower than SOT23)

### 1.3 Applications

Driver circuits

Switching in portable appliances

### 1.4 Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	25 °C $\leq$ T <sub>j</sub> $\leq$ 150 °C	-	-	30	V
I <sub>D</sub>	drain current	$T_{amb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see <u>Figure 1</u>	-	-	480	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C; see Figure 2	-	-	350	mW
Static cha	aracteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 0.2 \text{ A};$ $T_j = 25 ^\circ\text{C}; \text{ see } \frac{\text{Figure 8}}{100000000000000000000000000000000000$	-	-	1	Ω



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## 2. Pinning information

Table 2.	Pinning			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	S	source		
3	D	drain	2	
			Transparent top view	G
			SOT883 (SC-101)	mbb076 S

## 3. Ordering information

Table 3. Ordering information				
Type number	Package			
	Name	Description	Version	
PMZ1000UN	SC-101	leadless ultra small plastic package; 3 solder lands; body $1.0 \times 0.6 \times 0.5 \text{ mm}$	SOT883	

### 4. Marking

Table 4. Marking	codes
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Type number	Marking code
PMZ1000UN	6N

## 5. Limiting values

### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

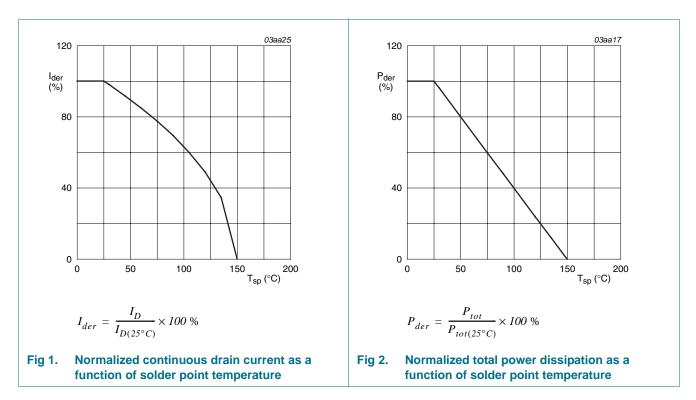
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	$25 \text{ °C} \leq T_j \leq 150 \text{ °C}$	-	30	V
$V_{DGR}$	drain-gate voltage	25 °C $\leq$ $T_{j}$ $\leq$ 150 °C; $R_{GS}$ = 20 $k\Omega$	-	30	V
$V_{GS}$	gate-source voltage		-8	+8	V
I <sub>D</sub>	drain current	$T_{amb} = 25 \ ^{\circ}C; V_{GS} = 10 \ V; see \frac{Figure 1}{1}$	-	480	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; $t_p \leq$ 10 $\mu s;$ pulsed	-	1.8	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C; see <u>Figure 2</u>	-	350	mW
T <sub>stg</sub>	storage temperature		-55	+150	°C
Tj	junction temperature		-55	+150	°C

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#### Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

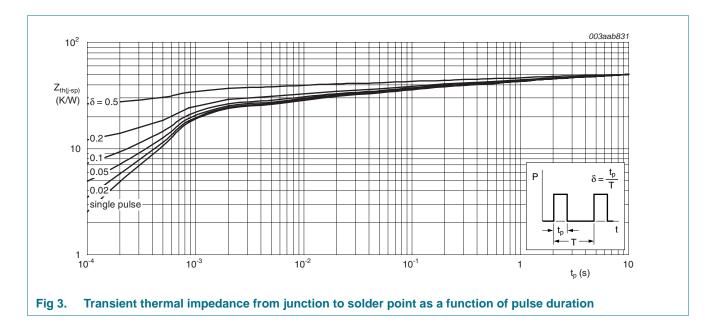
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Symbo	ol Parameter	Conditions	Min	Max	Unit
Source	e-drain diode				
ls	source current	T <sub>amb</sub> = 25 °C	-	480	mA
Electro	ostatic discharge				
$V_{\text{ESD}}$	electrostatic discharge voltage	HBM; C = 100 pF; R = 1.5 k $\Omega$	-	60	V
		MM; C = 200 pF	-	30	V
-					



## 6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point	see <u>Figure 3</u>	-	-	50	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		[1] -	-	355	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

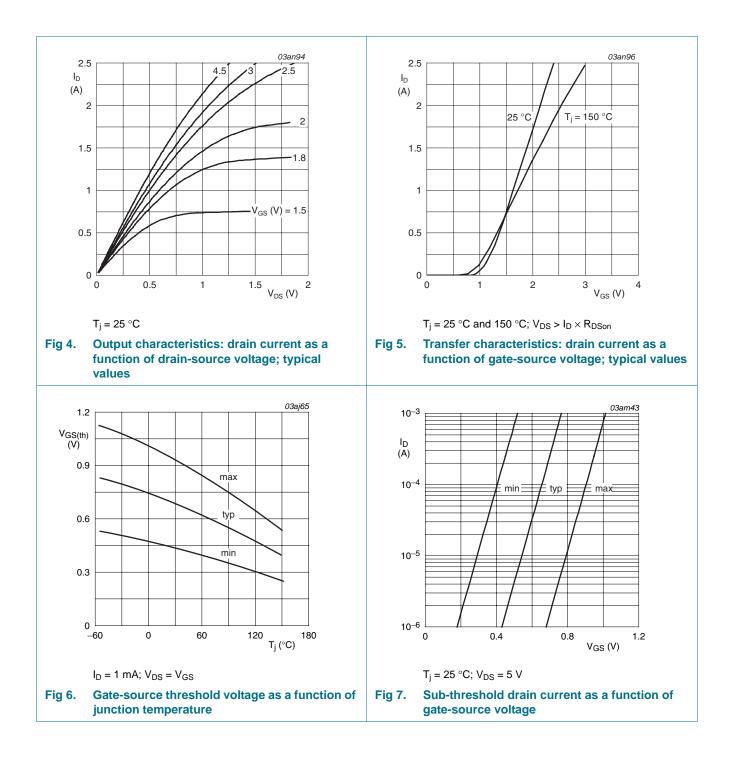


## 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown	$I_D = 10 \ \mu A; \ V_{GS} = 0 \ V$				
	voltage	T <sub>j</sub> = 25 °C	30	-	-	V
		T <sub>j</sub> = −55 °C	27	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D$ = 0.25 mA; $V_{DS}$ = $V_{GS}$ ; see <u>Figure 6</u> and <u>7</u>				
		T <sub>j</sub> = 25 °C	0.45	0.7	0.95	V
		T <sub>j</sub> = 150 °C	0.25	-	-	V
		T <sub>j</sub> = −55 °C	-	-	1.15	V
I <sub>DSS</sub> drain leakage current	drain leakage current	$V_{DS} = 30 \text{ V}; \text{ V}_{GS} = 0 \text{ V}$				
		T <sub>j</sub> = 25 °C	-	-	1	μA
		T <sub>j</sub> = 150 °C	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = \pm 8 \text{ V}; V_{DS} = 0 \text{ V}$	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = 4.5 V; $I_D$ = 0.2 A; see <u>Figure 8</u>				
	resistance	T <sub>j</sub> = 25 °C	-	-	1	Ω
		T <sub>j</sub> = 150 °C	-	-	1.5	Ω
		V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 0.1 A; <u>Figure 8</u>	-	-	1.1	Ω
		V <sub>GS</sub> = 1.8 V; I <sub>D</sub> = 0.075 A; <u>Figure 8</u>	-	-	1.4	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 1 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	0.89	-	nC
Q <sub>GS</sub>	gate-source charge	see <u>Figure 9</u> and <u>10</u>	-	0.1	-	nC
Q <sub>GD</sub>	gate-drain charge		-	0.2	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	43	-	pF
C <sub>oss</sub>	output capacitance	see Figure 11	-	7.7	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	4.8	-	pF
d(on)	turn-on delay time	$V_{DS} = 15 \text{ V}; \text{ R}_{L} = 15 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	4	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \ \Omega$	-	7.5	-	ns
d(off)	turn-off delay time		-	18	-	ns
f	fall time		-	4.5	-	ns
Source-o	Irain diode					
V <sub>SD</sub>	source-drain voltage	$I_{S} = 0.3 \text{ A}; V_{GS} = 0 \text{ V}; \text{ see } \frac{\text{Figure 11}}{1}$	-	0.76	1.2	V

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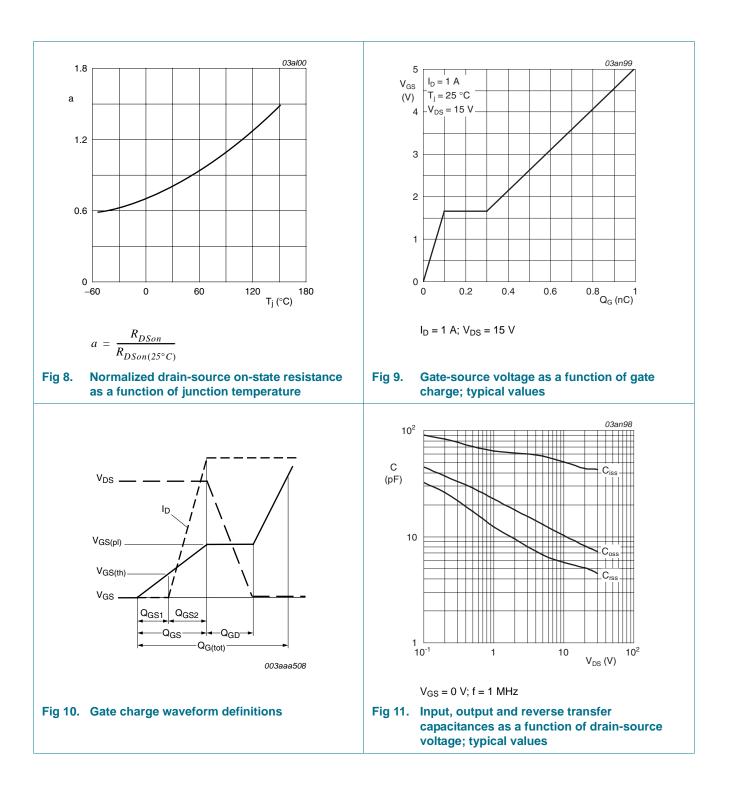


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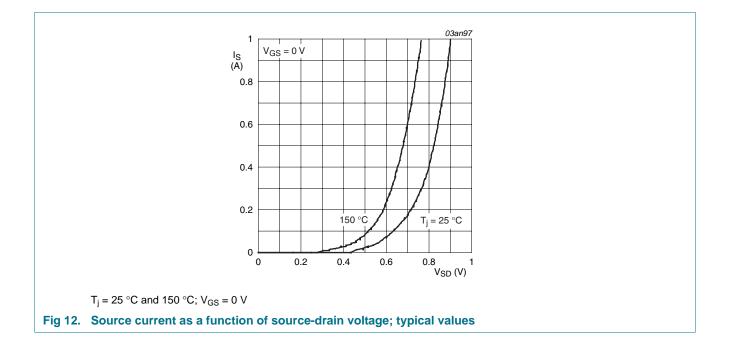


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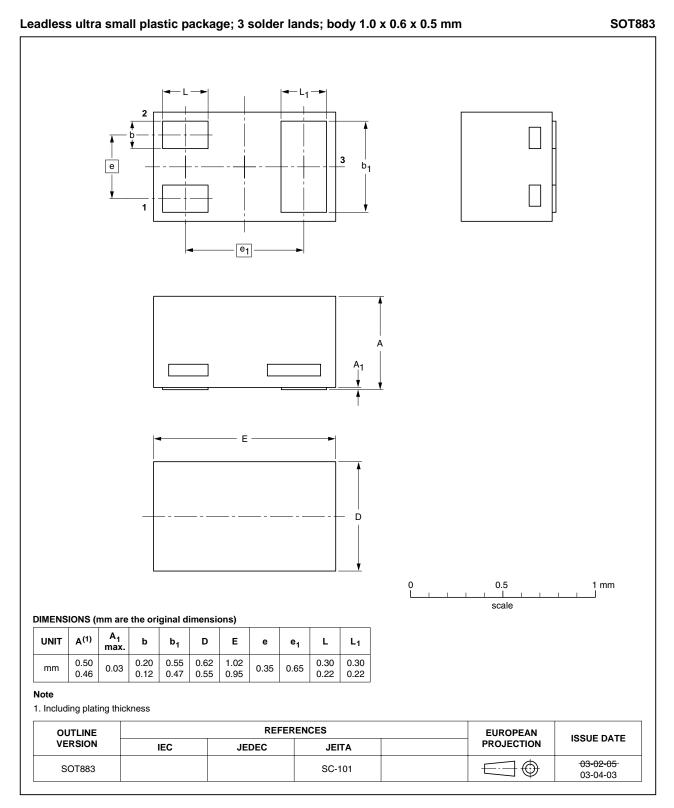
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### 8. Package outline

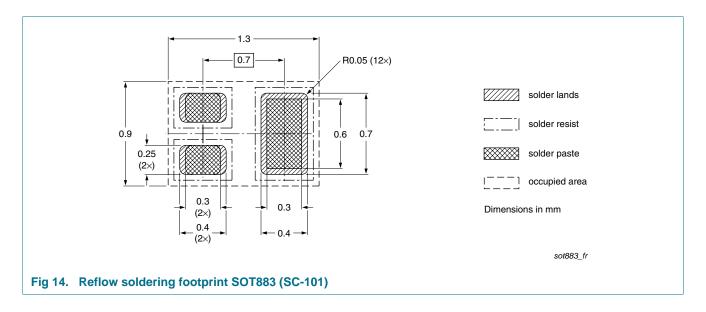


### Fig 13. Package outline SO883 (SC-101)

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## 9. Soldering



## **10. Revision history**

Table 8.Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PMZ1000UN v.2	20100917	Product data sheet	-	PMZ1000UN_1
Modifications:	<ul> <li>Modification</li> </ul>	ns of thermal parameters		
	Section 11 '	Legal information": updated		
PMZ1000UN_1	20100224	Product data sheet	-	-

## 11. Legal information

#### 11.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions"

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